



EO-532-P-Subnano/0.5mJ

**HIGH ENERGY DIODE
PUMPED ALL-SOLID-STATE
Q-SWITCHED LASER**

High energy diode pumped all solid state Q-switched laser at 532nm has the features of high single pulse energy, short pulse duration, and high peak power, which is widely used in Micromachining of hard and brittle materials, scientific research, OPO, and so on.

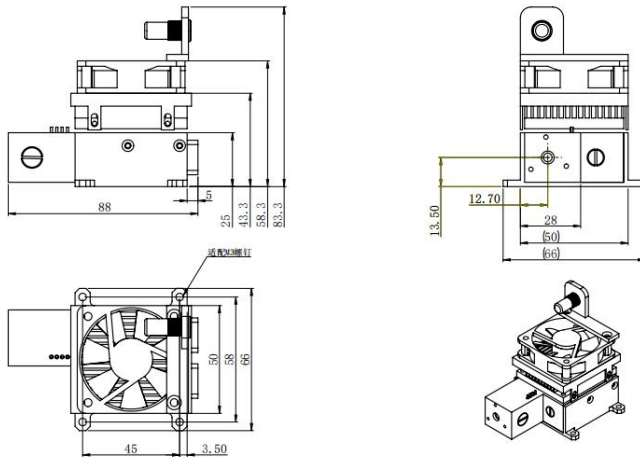


SPECIFICATIONS

| | |
|------------------------------------|-------------------------------------|
| Wavelength (nm) | 532±1 |
| Operating mode | Q-switched: PM (Passive Modulation) |
| Single pulse energy (mJ) | 0.5 |
| Pulse duration (ns) | <1 |
| Rep. rate (kHz) | 500Hz, 1kHz, 2kHz optional, EXT |
| Energy stability (rms) | <5%, <4% |
| Beam divergence, full angle (mrad) | <3 |
| Beam diameter (mm) | ~3 |
| Warm-up time (minutes) | <15 |
| Beam height from base plate (mm) | 13.5 |
| Cooled method | Air cooled |
| Operating temperature (°C) | 15~30 |
| Power supply (24V DC) | PSU-DPS-Subnano |
| Expected lifetime (pulses) | 10 ⁹ |
| Warranty period | 1 year |

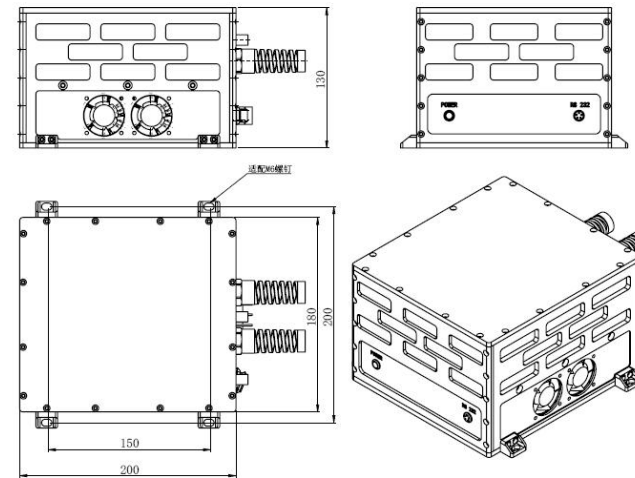


EO-532-P-Subnano



88(L)×66(W)×83.3(H)mm³, 1kg

PSU-DPS-P-Subnano



200 (L) ×200(W) ×130(H) mm³, 6 kg